

BTA06 and BTB06 Series

SNUBBERLESS™, LOGIC LEVEL & STANDARD

6A TRIACs

Table 1: Main Features

Symbol	Value	Unit
I _{T(RMS)}	6	А
V _{DRM} /V _{RRM}	600 and 800	V
I _{GT (Q1})	5 to 50	mA

DESCRIPTION

Available either in through-hole or surface-mount packages, the **BTA06** and **BTB06** triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation in light dimmers, motor speed controllers,...

The snubberless and logic level versions (BTA/ BTB...W) are specially recommended for use on inductive loads, thanks to their high commutation performances.

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at $2500V_{RMS}$) complying with UL standards (File ref.: E81734).

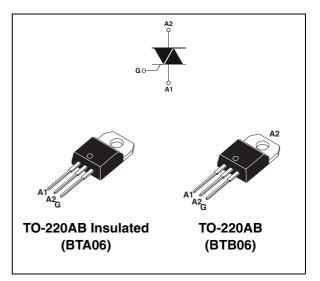


Table 2: Order Codes

Part Number	Marking
BTA06-xxxxxRG	See page table 8 on
BTB06-xxxxxRG	page 6

Symbol	Paramet	Parameter					
I	RMS on-state current (full sine	TO-220AB	$TO-220AB \qquad T_{c} = 110^{\circ}C$		۸		
IT(RMS)	wave)	TO-220AB Ins.	T _c = 105°C	6	A		
Irou	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	60	А		
ITSM	current (full cycle, T_j initial = 25°C)	F = 60 Hz	t = 16.7 ms 63				
l²t	I ² t Value for fusing	t _p = 10 ms		21	A²s		
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 125°C	50	A/µs		
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125°C	4	А		
P _{G(AV)}	Average gate power dissipation	1	W				
T _{stg} T _j	Storage junction temperature range Operating junction temperature range	- 40 to + 150 - 40 to + 125	°C				

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Tables 4: Electrical Characteristics ($T_j = 25^{\circ}C$, unless otherwise specified)

SNUBBERLESS and Logic Level (3 quadrants)

Symbol	Test Conditions	ns Quadrant			BTA06	BTB06		Unit
Symbol		Quaurant		TW	SW	CW	BW	Unit
I _{GT} (1)	$V_{D} = 12 V R_{I} = 30 \Omega$	- -	MAX.	5	10	35	50	mA
V _{GT}		- -	MAX.		1	.3		V
V _{GD}			MIN.	0.2				V
I _H (2)	I _T = 100 mA		MAX.	10	15	35	50	mA
l _l	I _G = 1.2 I _{GT}	-	MAX.	10	25	50	70	mA
'L		II	II MAA.	15	30	60	80	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $T_j = 125^{\circ}C$		MIN.	20	40	400	1000	V/µs
	$(dV/dt)c = 0.1 V/\mu s T_j = 125^{\circ}C$			2.7	3.5	-	-	
(dl/dt)c (2)	$(dV/dt)c = 10 V/\mu s$ T _j = 125°C		MIN.	1.2	2.4	-	-	A/ms
	Without snubber $T_j = 125^{\circ}C$;		-	-	3.5	5.3	

Standard (4 quadrants)

Symbol	Symbol Test Conditions			BTA06	BTB06	Unit
Symbol	Test conditions	Quadrant		С	В	
I _{GT} (1)	I _{GT} (1)		MAX.	25 50	50 100	mA
	$V_D = 12 V$ $R_L = 30 \Omega$	IV				
V _{GT}		ALL	MAX.	1	.3	V
V _{GD}	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_j = 125^{\circ}C \qquad \text{ALL}$		MIN.	0.2		V
I _H (2)	I _T = 500 mA		MAX.	25	50	mA
IL	$I_{G} = 1.2 I_{GT}$	I - III - IV	MAX.	40	50	mA
·L			IVI/A/A.	80	100	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open $T_j = 125^{\circ}C$		MIN.	200	400	V/µs
(dV/dt)c (2)	$(dI/dt)c = 2.7 \text{ A/ms}$ $T_j = 125^{\circ}$	C	MIN.	5	10	V/µs

Table 5: Static Characteristics

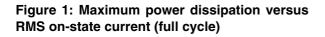
Symbol	Test C	Test Conditions			Unit
V _{TM} (2)	I _{TM} = 8.5 A t _p = 380 μs	$T_j = 25^{\circ}C$	MAX.	1.55	V
V _{t0} (2)	Threshold voltage	T _j = 125°C	MAX.	0.85	V
R _d (2)	Dynamic resistance	T _j = 125°C	MAX.	60	mΩ
I _{DRM}	V _{DBM} = V _{BBM}	$T_j = 25^{\circ}C$	MAY	5	μA
I _{RRM}		T _j = 125°C	MAX1		mA

Note 1: minimum I_{GT} is guaranted at 5% of I_{GT} max.

Note 2: for both polarities of A2 referenced to A1.

Symbol	Paramete	Value	Unit	
Bu a x	lunction to case (AC)	TO-220AB	1.8	°C/W
R _{th(j-c)} Junction to case (AC)	TO-220AB Insulated	2.7	0/00	
R _{th(j-a)}	Junction to ambient	TO-220AB TO-220AB Insulated	60	°C/W

Table 6: Thermal resistance



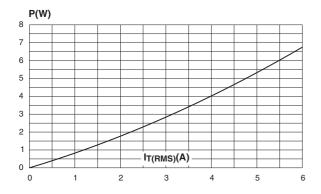


Figure 3: Relative variation of thermal impedance versus pulse duration

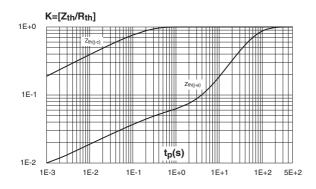
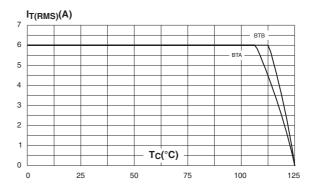
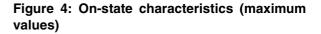
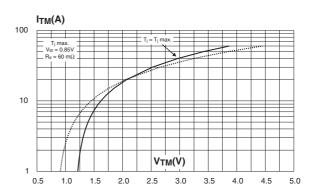




Figure 2: RMS on-state current versus case temperature (full cycle)







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Figure 5: Surge peak on-state current versus number of cycles

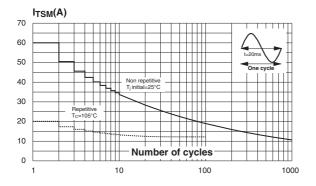


Figure 7: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

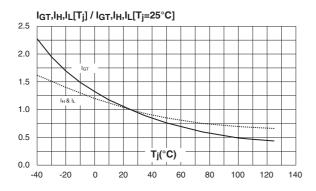


Figure 9: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (Standard types)

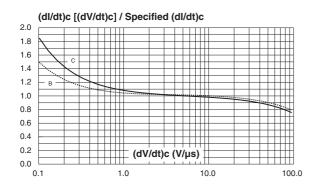


Figure 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of l^2t

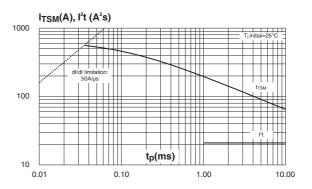


Figure 8: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (Snubberless & logic level types)

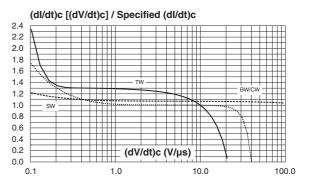
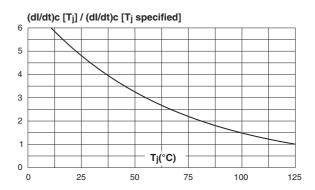


Figure 10: Relative variation of critical rate of decrease of main current versus junction temperature



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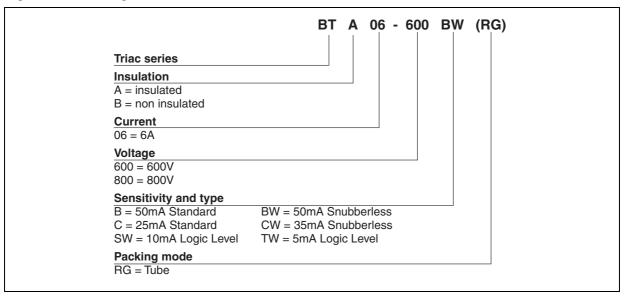


Table 7: Product Selector

Part Number	Voltag	e (xxx)	Sensitivity	Туре	
raitinumber	600 V	800 V	Jensitivity	туре	Package
BTA/BTB06-xxxB	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB06-xxxBW	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB06-xxxC	Х	Х	25 mA	Standard	TO-220AB
BTA/BTB06-xxxCW	Х	Х	35 mA	Snubberless	TO-220AB
BTA/BTB06-xxxSW	Х	Х	10 mA	Logic level	TO-220AB
BTA/BTB06-xxxTW	Х	Х	5 mA	Logic Level	TO-220AB

BTB: non insulated TO-220AB package

					DIMEN	SIONS		
		REF.		llimete	rs		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
в	с	Α	15.20		15.90	0.598		0.625
×	b2	a1		3.75			0.147	
		a2	13.00		14.00	0.511		0.551
	F	В	10.00		10.40	0.393		0.409
		b1	0.61		0.88	0.024		0.034
		b2	1.23		1.32	0.048		0.051
14 I3		С	4.40		4.60	0.173		0.181
	c2	c1	0.49		0.70	0.019		0.027
	<u> </u>	c2	2.40		2.72	0.094		0.107
12 a2		е	2.40		2.70	0.094		0.106
		F	6.20		6.60	0.244		0.259
	M	ØI	3.75		3.85	0.147		0.151
	•→ c1 → •	14	15.80	16.40	16.80	0.622	0.646	0.661
6		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	

Figure 12: TO-220AB (insulated and non insulated) Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BTA/BTB06-xxxyzRG	BTA/BTB06-xxxyz	TO-220AB	2.3 g	50	Tube

Note: xxx = voltage, yy = sensitivity, z = type

Table 9: Revision History

Date	Revision	Description of Changes
Apr-2002	5A	Last update.
13-Feb-2006	6	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.

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